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(54) **METHOD OF FORMING A VERTICAL TRANSISTOR**

(75) Inventors: **Nirmal Ramaswamy**, Boise, ID (US);
Gurtej S. Sandhu, Boise, ID (US);
Cem Basceri, Reston, VA (US); **Eric R. Blomiley**, Boise, ID (US)

(73) Assignee: **Micron Technology, Inc.**, Boise, ID (US)

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See application file for complete search history.

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Primary Examiner—Trung Dang

(74) Attorney, Agent, or Firm—Wells St. John P.S.

(57) **ABSTRACT**

The invention includes methods of forming epitaxial silicon-comprising material and methods of forming vertical transistors. In one implementation, a method of forming epitaxial silicon-comprising material includes providing a substrate comprising monocrystalline material. A first portion of the monocrystalline material is outwardly exposed while a second portion of the monocrystalline material is masked. A first silicon-comprising layer is epitaxially grown from the exposed monocrystalline material of the first portion and not from the monocrystalline material of the masked second portion. After growing the first silicon-comprising layer, the second portion of the monocrystalline material is unmasked. A second silicon-comprising layer is then epitaxially grown from the first silicon-comprising layer and from the unmasked monocrystalline material of the second portion. Other aspects and implementations are contemplated.

27 Claims, 13 Drawing Sheets

